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Kiyoteru Kobayashi, Aran Suzuki, Kokichi Ishikawa

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in low-pressure chemical vapor deposited silicon nitride films**

Kiyoteru Kobayashi, Aran Suzuki, and Kokichi Ishikawa

Graduate School of Engineering, Tokai University,

4-1-1 Kitakaname, Hiratsuka, Kanagawa 259-1292, Japan

\*Corresponding author: Kiyoteru Kobayashi

Course of Electrical and Electronic System

Graduate School of Engineering, Tokai University

4-1-1 Kitakaname, Hiratsuka, Kanagawa 259-1292, Japan

E-mail: kkbys@keyaki.cc.u-tokai.ac.jp

Phone: +81-463-58-1211 (ext. 4100); Fax: +81-463-59-4014

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